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[Continued on next page]

(54) **Title**: PROCESS FOR MANUFACTURING A STRUCTURE COMPRISING A GERMANIUM LAYER ON A SUBSTRATE

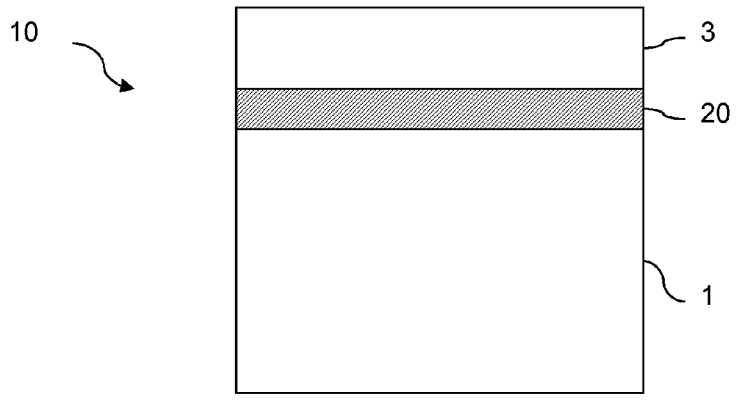


FIG. 1

(57) **Abstract**: The present invention relates to a process for manufacturing a structure comprising a germanium layer (3) on a support substrate (1), characterised in that it comprises the following steps: (a) formation of an intermediate structure (10) comprising said support substrate (1), a silicon oxide layer (20) and said germanium layer (3), the silicon oxide layer (20) being in direct contact with the germanium layer (3), (b) application to said intermediate structure (10) of a heat treatment, in a neutral or reducing atmosphere, at a defined temperature and for a defined time, to diffuse at least part of the oxygen from the silicon oxide layer (20) through the germanium layer (3).

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